



INFORMATION DISCLOSURE CITATION

PAGE 1 OF 3

Atty Docket No.
OPE-026Serial No.
10/700,016Applicant
Geoff W. Taylor et al.Filed
November 3, 2003Group
2813

US PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Sub- class	Filing date if approp.
MDI	A	3,919,656	11/11/75	Sokal et al.	330	51	—
	B	4,424,525	1/3/84	Mimura	357	23	—
	C	4,658,403	4/14/87	Takiguchi et al.	372	96	—
	D	4,683,484	7/28/87	Derkits, Jr.	357	16	—
	E	4,806,997	2/21/89	Simmons et al.	357	16	—
	F	4,814,774	3/21/89	Herczfeld	342	372	—
	G	4,827,320	5/2/89	Morkoc et al.	357	22	—
	H	4,829,272	5/9/89	Kameya	333	139	—
	I	4,899,200	2/6/90	Shur et al.	357	30	—
	J	4,949,350	8/14/90	Jewell et al.	372	45	—
	K	5,010,374	4/23/91	Cooke et al.	357	16	—
	L	5,105,248	4/14/92	Burke et al.	357	24	—
	M	5,202,896	4/13/93	Taylor	372	50	—
	N	5,337,328	8/9/94	Lang et al.	372	45	—
	O	5,386,128	1/31/95	Fossum et al.	257	183.1	—
	P	5,422,501	6/6/95	Bayraktaroglu	257	195	—
	Q	5,436,759	7/25/95	Dijaili et al.	359	333	—
	R	5,698,900	12/16/97	Bozada et al.	257	744	—
	S	6,031,243	2/29/00	Taylor	257	13	—
	T	6,043,519	3/28/00	Shealy et al.	257	195	—
	U	US 20020067877	6/6/02	Braun et al.			—
	V	5,288,659	02/94	Koch et al.	438	31	—
	W	5,452, 118	09/95	Maruska	398	204	—
↓	X	5,999,553	12/99	Sun	372	50	—

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INFORMATION DISCLOSURE CITATION

PAGE 2 OF 3

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Examiner Initials		Document No.	Date	Name	Class	Sub- class	Filing date if approp.
MDH	A	6,479,844	11/02	Taylor	257	98	—
	B	6,720,584	04/04	Hata et al.	257	98	—
	C	6,483,170	11/19/02	Johansson	257	580	—
	D	6,239,475	05/29/01	Johansson et al.	257	488	—
	E	6,037,616	03/12/00	Amamiya	257	198	—
Y	F	5,003,366	03/26/91	Mishimi et al.	257	197	—
	G						
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INFORMATION DISCLOSURE CITATION

PAGE 3 OF 3

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

MDH	AA	<u>10-Gb/s High-Speed Monolithically Integrated photoreceiver Using InGaAs p-i-n PD and Planar Doped InAlAs/InGaAs HEMT's</u> by Akahori et al, IEEE Photonics Technology Letters, Vol 4, No. 7, July 1992
	BB	<u>10-Gbit/s InP-Based High-Performance Monolithic Photoreceivers Consisting of p-i-n Photodiodes and HEMT's</u> by Takahata et al., IEICE Trans. Electron., Vol. E83-C, No. 6 June 2000
	CC	<u>10 Ghz Bandwidth Monolithic p-i-n Modulation-doped Field Effect Transistor Photoreceiver</u> by Dutta et al., Appl. Phys. Lett., Vol. 63, No. 15, 11 October 1993
	DD	<u>20 Gbit/s Long Wavelength Monolithic Integrated Photoreceiver Grown on GaAs</u> by Hurm, et al., Electronics Letters, Vol. 33, No. 7, 27th March 1997
	EE	<u>Monolithic Integrated Optoelectronic Circuits</u> by Berroth et al., Fraunhofer Institute for Applied Solid State Physics (IAF), Germany, IEEE 1995
	FF	<u>Heterojunction Field-Effect Transistor (HFET)</u> , Reprinted from Electronics Letters, Vol 22, No. 15, pp. 784-786, 17th July 1986
	GG	<u>High Temperature Annealing of Modulation Doped GaAs/AlGaAs Heterostructures for FET Applications</u> by Lee et al., 1983 IEEE/Cornell Conf. On High-Speed Semiconductor Devices & Ckts, 8/83
	HH	<u>Submicrometre Gate Length Scaling of Inversion Channel Heterojunction Field Effect Transistor</u> by Kiely et al., Electronics Letters, Vol. 30, No. 6 17th March 1994
	II	<u>Theoretical and Experimental Results for the Inversion Channel Heterostructure Field Effect Transistor</u> by Taylor et al., IEE Proceedings-G, Vol. 140, No. 6, December 1993
	jj	<u>Transmitting Transistor Design: RF Transmitting Transistor and power amplifier fundamentals</u> , Phillips Semiconductors; March 23, 1998
	kk	<u>Thermally Stable Ohmic Contacts to n-type GaAs. VIII. Sputter-deposited InAs Contacts</u> ; HJ Kim, Masanori Murakami, SL Wright, M. Norcott, WH Price and D. La Tulipe; 4/11/90
	ll	<u>Thermally Stable Ohmic Contact to n-type GaAs IX. Sputter-deposited InAs Contacts NiIn(mn) and NiIn(w) Contact Metals</u> , J. Applied Physics, Vol. 70, 11/12/91 pgs. 7443-7448
V/	mm	<u>Transferred Substrate HBT's with 254 GHz²F.</u> D. Mensa et al.; Electron Lett. 4/99; 35(7) pp. 605-606

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